CMOS VOLTAGE DETECTOR IC with Delay Time Circuit

BD52XXG/FVE BD53XXG/FVE

ROHM's BD52XXG/FVE and BD53XXG/FVE are series of high-accuracy, low-power VOLTAGE DETECTOR ICs with a CMOS process. These series can set delay time by external capacitor. For flexible choice according to the application, BD52XXG/FVE series with N channel open drain output and BD53XXG/FVE series with CMOS output are available in 38 voltage types which detection voltage is from 2.3V to 6.0V in steps of 0.1V in different packages, totaling 152 models.

Applications

Every kind of appliances with microcontroller and logic circuit

Features

- 1) Detection voltage: 0.1V step line-up 2.3 to 6.0V (Typ.)
- 2) High-accuracy detection voltage: ±1.5% guranteed (Ability ±1%)
- 3) Ultra low current consumption: 0.85µA typ. (Output is High.)
- 4) Delay time can be set by external capacitor.
- 5) Nch open drain output (BD52XXG/FVE series), CMOS output (BD53XXG/FVE series)
- 6) Small package of VSOF5(EMP5)(BD52XXFVE/BD53XXFVE), and SSOP5(SMP5C2)(BD52XXG/BD53XXG)

Selection guide

For BD5XXXX series, detection voltage, output circuit types (Refer to the block diagram at P3),and package (Refer to the block diagram at P14) can be selected for your own application.Part number of devices for each specification is shown below.

| Part No. | Specification | Contents |
|----------|----------------------|------------------------------------------------------------------------------------|
| 1 | Output circuit types | 2 : Open drain output 3 : CMOS output |
| 2 | Detection voltage | Ex. : VDET : described in each 0.1V step for 2.3V to 6.0V range (29 means 2.9V) |
| 3 | Package | G : SSOP5 (SMP5C2) FVE : VSOF5 (EMP5) |

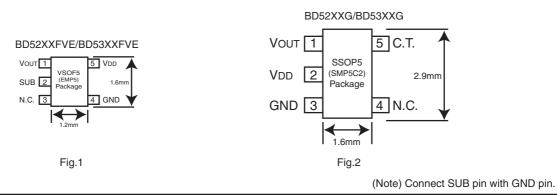
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● Line-up

| Detection voltage | Nch Open drain output | CMOS output | Detection v | oltage VDET (| V) Ta=25°C | Hysteresis voltage | Package |
|-------------------|-----------------------|---------------|-------------|---------------|-------------|-----------------------|-----------------------------|
| Voltage VDET | (BD52XXG/FVE) | (BD53XXG/FVE) | Min. | Тур. | Max. | (V,Typ.) | Fackage |
| 6.0V | BD5260G/FVE | BD5360G/FVE | 5.910 | 6.000 | 6.090 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 5.9V | BD5259G/FVE | BD5359G/FVE | 5.812 | 5.900 | 5.989 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 5.8V | BD5258G/FVE | BD5358G/FVE | 5.713 | 5.800 | 5.887 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 5.7V | BD5257G/FVE | BD5357G/FVE | 5.615 | 5.700 | 5.786 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 5.6V | BD5256G/FVE | BD5356G/FVE | 5.516 | 5.600 | 5.684 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 5.5V | BD5255G/FVE | BD5355G/FVE | 5.418 | 5.500 | 5.583 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 5.4V | BD5254G/FVE | BD5354G/FVE | 5.319 | 5.400 | 5.481 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 5.3V | BD5253G/FVE | BD5353G/FVE | 5.221 | 5.300 | 5.380 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 5.2V | BD5252G/FVE | BD5352G/FVE | 5.122 | 5.200 | 5.278 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 5.1V | BD5251G/FVE | BD5351G/FVE | 5.024 | 5.100 | 5.177 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 5.0V | BD5250G/FVE | BD5350G/FVE | 4.925 | 5.000 | 5.075 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 4.9V | BD5249G/FVE | BD5349G/FVE | 4.827 | 4.900 | 4.974 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 4.8V | BD5248G/FVE | BD5348G/FVE | 4.728 | 4.800 | 4.872 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 4.7V | BD5247G/FVE | BD5347G/FVE | 4.630 | 4.700 | 4.771 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 4.6V | BD5246G/FVE | BD5346G/FVE | 4.531 | 4.600 | 4.669 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 4.5V | BD5245G/FVE | BD5345G/FVE | 4.433 | 4.500 | 4.568 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 4.4V | BD5244G/FVE | BD5344G/FVE | 4.334 | 4.400 | 4.466 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 4.3V | BD5243G/FVE | BD5343G/FVE | 4.236 | 4.300 | 4.365 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 4.2V | BD5242G/FVE | BD5342G/FVE | 4.137 | 4.200 | 4.263 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 4.1V | BD5241G/FVE | BD5341G/FVE | 4.039 | 4.100 | 4.162 | VDETX 0.05 | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 4.0V | BD5240G/FVE | BD5340G/FVE | 3.940 | 4.000 | 4.060 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 3.9V | BD5239G/FVE | BD5339G/FVE | 3.842 | 3.900 | 3.959 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 3.8V | BD5238G/FVE | BD5338G/FVE | 3.743 | 3.800 | 3.857 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 3.7V | BD5237G/FVE | BD5337G/FVE | 3.645 | 3.700 | 3.756 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 3.6V | BD5236G/FVE | BD5336G/FVE | 3.546 | 3.600 | 3.654 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 3.5V | BD5235G/FVE | BD5335G/FVE | 3.448 | 3.500 | 3.553 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 3.4V | BD5234G/FVE | BD5334G/FVE | 3.349 | 3.400 | 3.451 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 3.3V | BD5233G/FVE | BD5333G/FVE | 3.251 | 3.300 | 3.350 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 3.2V | BD5232G/FVE | BD5332G/FVE | 3.152 | 3.200 | 3.248 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 3.1V | BD5231G/FVE | BD5331G/FVE | 3.054 | 3.100 | 3.147 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 3.0V | BD5230G/FVE | BD5330G/FVE | 2.955 | 3.000 | 3.045 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 2.9V | BD5229G/FVE | BD5329G/FVE | 2.857 | 2.900 | 2.944 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 2.8V | BD5228G/FVE | BD5328G/FVE | 2.758 | 2.800 | 2.842 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 2.7V | BD5227G/FVE | BD5327G/FVE | 2.660 | 2.700 | 2.741 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 2.6V | BD5226G/FVE | BD5326G/FVE | 2.561 | 2.600 | 2.639 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 2.5V | BD5225G/FVE | BD5325G/FVE | 2.463 | 2.500 | 2.538 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 2.4V | BD5224G/FVE | BD5324G/FVE | 2.364 | 2.400 | 2.436 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |
| 2.3V | BD5223G/FVE | BD5323G/FVE | 2.266 | 2.300 | 2.335 | | SSOP5 (SMP5C2)/VSOF5 (EMP5) |

Pin layout

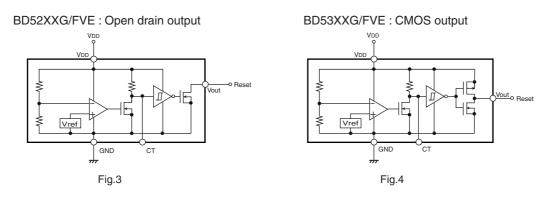
Pin layout of VSOF5(EMP5) and SSOP5(SMP5C2) is different as shown below. (Fig.1, Fig.2) When used as replacement, please consider the difference. (The detail of packages is shown at P14.)





Block diagram

Two output types can be used. One is BD52XXG/FVE (Left) of open drain output type, and the other is BD53XXG/FVE (Right) of CMOS output type.



Absolute maximum rating (Ta=25°C)

To prevent the functional deterioration or thermal damage of semiconductor devices and ensure their service life and reliability, they must be designed and reviewed in such a way that the absolute maximum rating can not be exceeded in any cases or even at any moment.

| | Parameter | Symbol | Limits | Unit | |
|-----------|------------------------------|-----------|------------------------|------|--|
| Power su | pply voltage | Vdd – GND | – 0.3 to + 10 | V | |
| Output | Nch Open drain output | Vout | GND – 0.3 to + 10 | V | |
| voltage | voltage CMOS output | | GND - 0.3 to VDD + 0.3 | v | |
| CT pin vo | | Vст | GND - 0.3 to VDD + 0.3 | V | |
| Power dis | ssipation (SSOP5(SMP5C2)) *3 | Pd | 540 | mW | |
| Power dis | ssipation (VSOF5(EMP5)) *2 | Pd | 210 | mW | |
| Operating | g temperature | Topr | – 40 to + 85 | °C | |
| Storage t | emperature | Tstg | – 55 to + 125 | °C | |

*1 Derating : 5.4mW/°C for operation above Ta=25°C *2 Derating : 2.1mW/°C for operation above Ta=25°C *3 When ROHM's standard board(70mmX70mmX1.6mm, glass epoxy board) is mounted.

Power supply voltage

This voltage is the applied voltage between VDD and GND. The applied voltage should not exceed the indicated value.

Output voltage

VOUT pin voltage should not exceed the indicated value. For Nch open drain output type, VDD applied voltage and VOUT pin H output voltage can be used independently. Both of them should not exceed the each indicated value.

Operating temperature range

The circuit function is guaranteed within the temperature range. However, the operating characteristics are different from that of Ta=25°C. If they are any questions about the extent of guarantee of circuit functions in this operating temperature range, please ask for more technical information.

• Storage temperature range

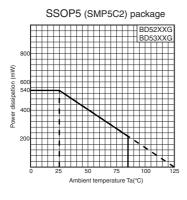
This IC can be stored up to this temperature range without deterioration of characteristics. However, an abrupt thermal shock of extreme temperature fluctuations may cause the deterioration of characteristics.



Power dissipation

Power consumption of the IC

Circuit current at ON/OFF is very small. Power consumption in output depends on each load connected with VOUT pin. Please note that total power consumption must be within a power dissipation range in the secure area of the entire operating temperature. Power dissipation of these packages; SSOP5 (SMP5C2) package (BD52XXG/ BD53XXG) Fig.5, and VSOF5 (EMP5) package (BD52XXFVE/BD53XXFVE) Fig.6 is shown below.



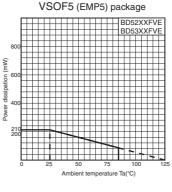


Fig.5 Thermal derating curve

Fig.6 Thermal derating curve

When it is used in the ambient temperature of (Ta)=25°C and more, make reference to each thermal derating characteristics of used package. Both Fig.5 and Fig.6 show these characteristic when ROHM's standard board (70mmX70mmX1.6mm, glass epoxy board) is mounted.

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Condi | Reference Data | | |
|-------------------------------------------|------------------|-----------|-----------|-----------|--------|-----------------------------------|-------------------|---------|--|
| Detection voltage temperature coefficient | Vdet/ ΔT | _ | ±100 | ±360 | ppm/°C | | | Fig.30 | |
| Hysteresis voltage | $\Delta V DET$ | VDETX0.03 | VDETX0.05 | VDETX0.08 | V | RL=470kΩ, VDD=L→H | →L | Fig.28 | |
| | | — | 0.80 | 2.40 | | | VDET=2.3 to 3.1V | - | |
| Circuit current | land | — | 0.85 | 2.55 | | | VDET=3.2 to 4.2V | | |
| when ON | IDD1 | | 0.90 | 2.70 | μΑ | VDD=VDET-0.2V | VDET=4.3 to 5.2V | | |
| | | | 0.95 | 2.85 | | | VDET=5.3 to 6.0V | Fig 25 | |
| | | — | 0.75 | 2.25 | | | VDET=2.3 to 3.1V | Fig.25 | |
| Circuit current | Inna | | 0.80 | 2.40 | | | VDET=3.2 to 4.2V | | |
| when OFF | IDD2 | | 0.85 | 2.55 | μΑ | VDD=VDET+2.0V | VDET=4.3 to 5.2V | | |
| | | — | 0.90 | 2.70 | | | VDET=5.3 to 6.0V | | |
| Min. operating voltage | Vopl | 0.95 | — | — | V | RL=470k , Vol 0.4V | RL=470k, Vol 0.4V | | |
| "L" output current | IOL1 | 0.4 | 1.2 | — | A | VDS=0.5V, VDD=1.2V | VDET=2.3 to 6.0V | | |
| | IOL2 | 2.0 | 5.0 | — | mA | VDS=0.5V, VDD=2.4V VDET=2.7 to 6. | | Fig.26 | |
| | | 0.7 | 1.4 | — | | VDS=0.5V, VDD=4.8V | VDET=2.3 to 4.2V | | |
| "H" output current | Іон | 0.9 | 1.8 | — | mA | VDS=0.5V, VDD=6.0V | VDET=4.3 to 5.2V | Fig.27 | |
| (Only BD53XXG/FVE series) | | 1.1 | 2.2 | — | | VDS=0.5V, VDD=8.0V | VDET=5.3 to 6.0V | | |
| | | VDDX0.3 | VDDX0.4 | VDDX0.6 | | | VDET=2.3 to 2.6V | | |
| CT pin | Vстн | VDDX0.3 | VDDX0.45 | VDDX0.6 | V | VDD=VDETX1.1 | VDET=2.7 to 4.2V | Fig.35 | |
| Threshold voltage | VCIH | VDDX0.35 | VDDX0.5 | VDDX0.6 | v | R∟=470k | VDET=4.3 to 5.2V | 1 lg.00 | |
| | | VDDX0.4 | VDDX0.5 | VDDX0.6 | | | VDET=5.3~6.0V | | |
| CT pin | RCT | 5.5 | 9 | 12.5 | MΩ | VDD=VDETX1.1, VCT=0. | 5V *1 | Fig.36 | |
| OT nin "I " ourront | ICT1 | 15 | 40 | — | 11.4 | VCT=0.1V,VDD=0.95V | *1 | | |
| CT pin "L" current | ICT2 | 150 | 240 | — | μΑ | VCT=0.5V,VDD=1.5V | - Fig.37 | | |
| Output leak current | lleak | _ | _ | 0.1 | μΑ | VDD=VDS=10V *1 | | Fig.32 | |

*1 Operation is guaranteed for Ta=25°C. Note) RL is not necessary for CMOS output type. Note) Minimum operating voltage VOUT output becomes inconsistent if the VDD is equal to or lower than the operating limit voltage. It goes open, H, or L. Note) Hysteresis voltage=(Reset release voltage)-(Reset detection voltage) [V]

Term explanation

(1) Detection voltage (VDET)

: VDD voltage when the output (Vout) goes from "H" to "L" . ORelease voltage (VDET+ Δ VDET) : VDD voltage when output (Vout) goes from "L" to "H".

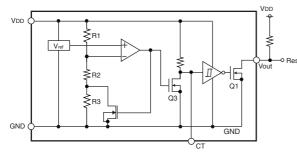
③Hysteresis voltage (Δ VDET)

: The difference between detection voltage and release voltage. Malfunction due to noise in VDD (within hysteresis voltage) could be avoided by hysteresis voltage.



Operating explanation

Ex.) For both open drain type (Fig.7) and CMOS output type (Fig.8), detection voltage and release voltage are threshold voltage. When voltage applied to VDD pin reaches each threshold voltage, VOUT pin voltage goes "H"→ "L" or "L"→ "H". BD52XXG/FVE and BD53XXG/FVE incorporate delay time circuit that can set delay time by the external capacitor when output goes"L"→ "H". BD52XXG/FVE series are open drain types and pull-up resistor must be connected to VDD, or other power supply. (In this case, output (VOUT) H voltage is VDD, or other power supply voltage.)



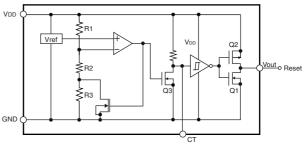


Fig.7 (BD52XX type Internal block diagram)



• SWEEP DOWN for VDD

•When VDD is equal to or more than the release voltage (VDET+∆VDET), CT pin voltage becomes VDD (External capacitor is in charging mode.) and output VOUT is in "H" mode. (Nch output transistor Q1 is OFF, Pch output transistor Q2 is ON.) When VDD is gradually decreased, Q3 connected to CT pin in the detection voltage (VDET) switches OFF to ON, external capacitor is discharged, and CT pin voltage becomes decreased. When the CT pin voltage is lower than the threshold voltage of next inverter, output (VOUT) turns "L". (Nch output transistor Q1 is ON, Pch output transistor Q2 is OFF.)

• SWEEP UP for VDD

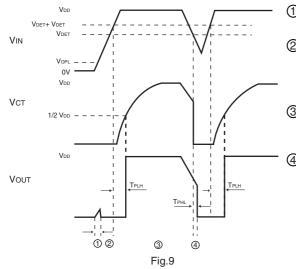
When VDD is equal to or lower than the detection voltage (VDET), CT pin voltage is L voltage (External capacitor is in discharging mode and Q3 is ON), output VOUT is in "L" mode. When VDD is gradually increased, Q3 is OFF in the release voltage (VDET+ΔVDET) and CT pin external capacitor becomes to be charged through resistor R1 in the IC. When the CT pin voltage is more than the threshold voltage of next inverter, output (VOUT) goes from "L" to "H". (Nch output transistor Q1 is OFF, Pch output transistor Q2 is ON.) Delay time is the time when output VOUT goes from "L" to "H" after the VDD is more than the release voltage. (VDET+ΔVDET) Delay time can be set freely by the CT pin external capacitor. (Usage is shown at P10)

•Some hysteresis is given such a way that the release voltage is the detection voltageX(1.05 Typ.).

• The output becomes inconsistent if the VDD is equal to or lower than the operating limit voltage.

Timing waveform

Ex.) The relation between input voltage VDD and output voltage VOUT when VDD is increased and decreased is shown below. (Circuit is shown in Fig7, Fig.8)



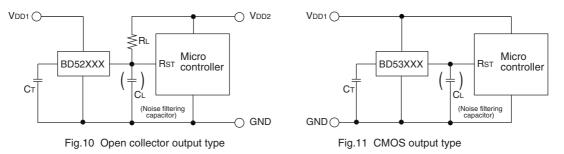
- (1) If the VDD is equal to or lower than the operating limit voltage (VOPL) at power-up, the output is inconsistent.
- ② When the VDD is equal to or more than the VOPL and the VDD is equal to or more than the reset release voltage (VDET+∆VDET), CT pin voltage (VCT) is "L" and output (VOUT) is also "L".
- ③ When the VDD is equal to or more than reset release voltage (VDET+ΔVDET), VOUT goes from "L" to "H" with a delay of TPLH set by the capacitor that is connected to CT pin.
- (4) If the VDD goes below the detection voltage (VDET) at power-down or instantaneous power failure, VOUT turns L with a delay of TPHL. See Fig.16 for the reference waveform. The potential difference between the detection voltage and the release voltage is called hysteresis (Δ VDET). The products are designed so as to prevent power supply fluctuation within this hysteresis from causing fluctuation in output in order to avoid malfunction due to noise.



Voltage detectors

Application circuit

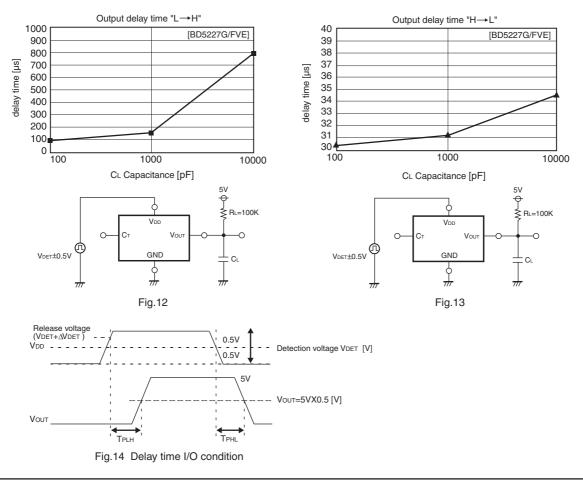
1) Application circuit as ordinal supply detection reset is shown below.



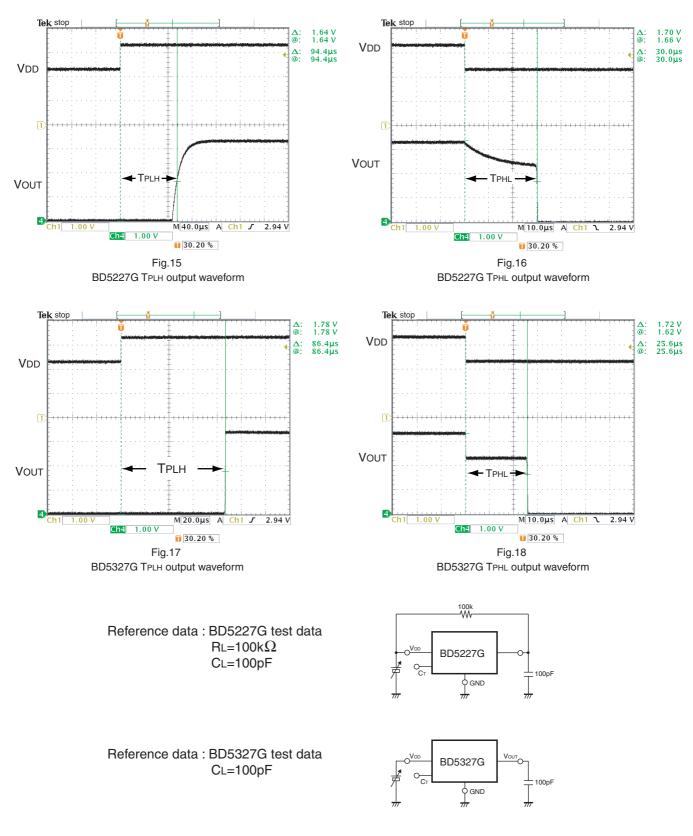
Output type of BD52XXG/FVE series (Open drain type) and BD53XXG/FVE series (CMOS type) is different. An example of usage is shown below.

- (1) When the power supply of microcontroller (VDD2) and power supply for the reset detection (VDD1) is different. Provide RL for the output of a product with open drain output (BD52XXG/FVE series) on the VDD2 side, as shown in Fig.10.
- ② When the power supply of microcontroller and that of reset is same (VDD1). A product with CMOS output (BD53XXG/FVE series) can be used as shown in Fig.11. Or if RL is provided with open drain output (BD52XXG/FVE series) on the VDD1 side, it can be used.

When the capacitor CL for noise filtering is connected to VOUT pin (reset signal input pin of microcontroller), make a setting in consideration of the wave rounding of the rise and fall of VOUT pin.

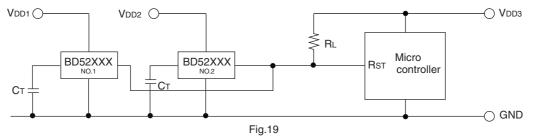






ROHM

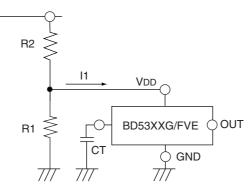
2)Application circuit when microcontroller is reset with OR connection of the two types of the detection voltage is shown below.



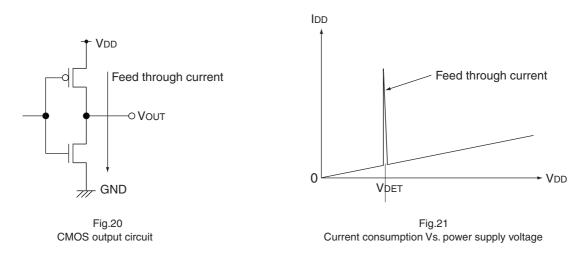
When there is more than one system power supply and it is necessary to individually monitor the power supply (VDD1, VDD2) to reset the microcontroller, open drain output type BD52XXG/FVE series can be connected to form an OR circuit as shown in Fig.19 for pulling up to an arbitrary voltage (VDD3) to adjust the H voltage of the output to the microcontroller power supply (VDD3).

For applications that voltage divided by resistance is inputted to input pin (VDD) of the IC if BD53XXG/FVE with CMOS output is used, the feed through current is flowed instantly and it may cause malfunction (Oscillation at output etc.) when output goes "H" \leftrightarrow "L". (Feed through current is the current flowed from VDD into GND instantly when output goes "H" \leftrightarrow "L".)

V1



Voltage drop ([Feed through current I1] X [Input resistor R2]) is occurred by the feed through current when output goes "L" to "H", and input voltage is decreased. When input voltage is decreased and become to be lower than detection voltage, output goes "H" to "L". At this time, no feed through current flows for output L and no voltage drop occurs. And output goes "L" to "H" again, feed through current flows and voltage drop is occurred. This operation is repeated. This means oscillation.



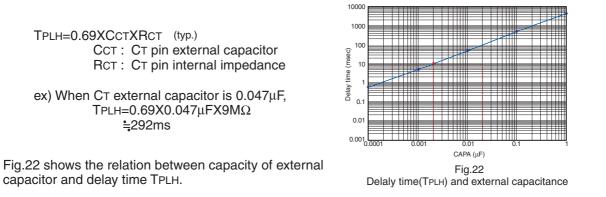


Establishment of RESET transfer delay time

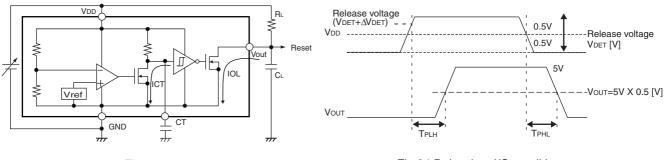
Delay time TPLH at the rise of VDD can be established by CCT connected to CT pin.

• Delay time at the rise of VDD TPLH : Time until when VOUT is 1/2 of VDD after the rise of VDD, and beyond the release voltage (VDET+ Δ VDET).(See P7).

Expression (When the threshold voltage of next inverter connected to CT pin is 1/2 of VDD.)



• Delay time at the fall of VDD TPHL : Time until when VOUT is 1/2 of VDD after across the detection voltage (Vs).







TPHL=TA+TB+TC

 $T_{A} = \frac{CL X VDET}{IOL}$: Delay time by external CL, RL CL : Capacity of external capacitor beween VOUT pin and GND VDET : Detection voltage IOL : "L" output current

(Make sure to test in actual because it depends on detection voltage.) Reference : VDET=2.4V, VDD=2.4V About 5mA : typ.

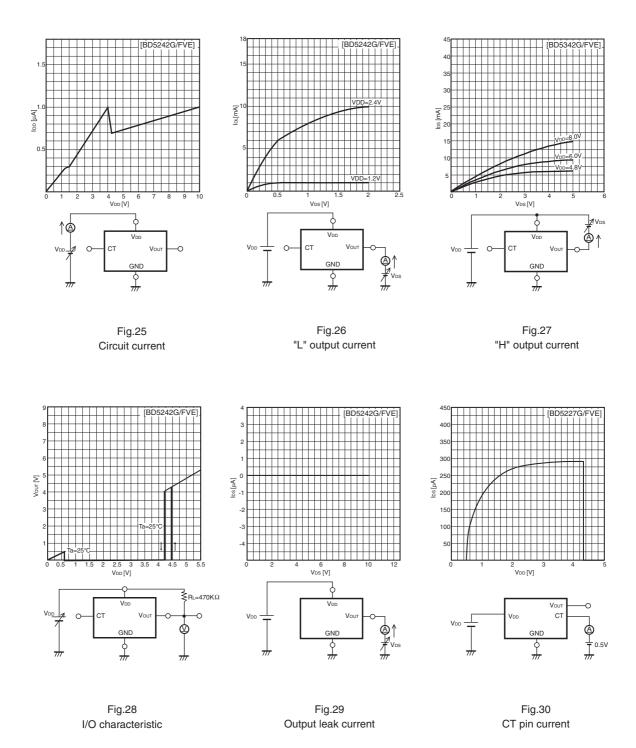
 $T_{B} = \frac{CT X V_{DET}}{I_{CT}}$: Delay time by external C of CT pin

CT : External capacitor between CT pin and GND VDET : Detection voltage ICT : Output current of CT pin

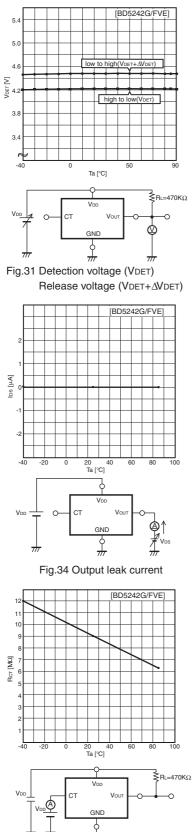
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Characteristic data (Reference data)







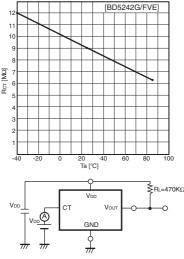


Fig.37 CT pin impedance

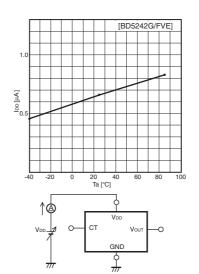
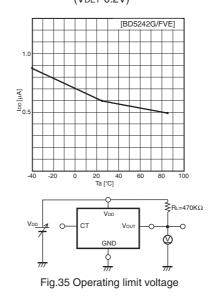


Fig.32 Circuit current when ON (VDET-0.2V)

 π



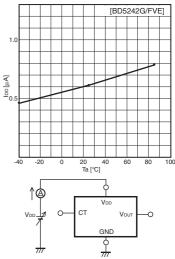
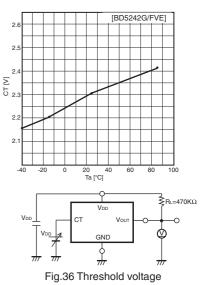


Fig.33 Circuit current when OFF (VDET+0.2V)



Taping specification 1)Dimension of tape

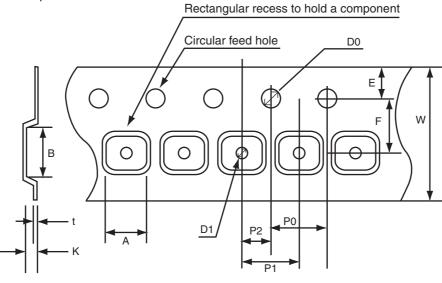
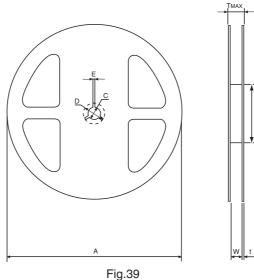


Fig.38

| Package | SSOP5 (S | MP5C2) | | | | | | | | i | | (mm) |
|-----------|-----------|----------|---------------------------|---------|-------------------|----------|---------|---------|----------|-----------|----------|---------|
| Symbol | А | В | D0 | D1 | E | F | P0 | P1 | P2 | t | К | W |
| Dimension | 3.2±0.1 | 3.1±0.1 | 1.5 ^{+0.1} -0 | 1.1±0.1 | 1.75 <u>+</u> 0.1 | 3.5±0.05 | 4.0±0.1 | 4.0±0.1 | 2.0±0.05 | 0.3±0.05 | 1.3±0.1 | 8.0±0.2 |
| Package | VSOF5 (EM | 1P5) | | | | | | | | | | (mm) |
| Symbol | А | В | D0 | D1 | E | F | P0 | P1 | P2 | t | К | W |
| Dimension | 1.83±0.1 | 1.83±0.1 | 1.5 ^{+0.1} | 0.5±0.1 | 1.75 <u>+</u> 0.1 | 3.5±0.05 | 4.0±0.1 | 4.0±0.1 | 2.0±0.05 | 0.25±0.05 | 0.75±0.1 | 8.0±0.2 |

2)Dimension of reel



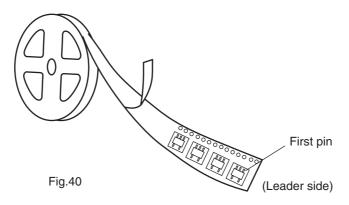
в

| Symbol | А | В | С | D | E | W | t | TMax. | | | | | |
|-----------|----------|-----------------|----------|-----------|----------|---------|-----------------------------------|-------|--|--|--|--|--|
| Dimension | 180 Max. | 60 <u>+</u> 2.0 | 13.0±0.5 | 20.2 Min. | 1.5 Min. | 9.0±0.3 | Label side(1.0) Back side(1.2) | 17.4 | | | | | |

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3)Standard packaged quantity and IC direction

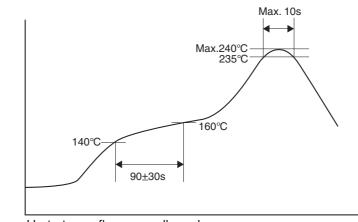
The standard packaged quantity is 3,000 pcs/reel. Orders should be in multiples of the standard packaged quantity. The ICs are TR oriented (as shown below).



Recommended mounting conditions

- SSOP5(SMP5C2) allows either reflow or flow soldering mounting.
- VSOF5(EMP5) allows reflow mounting. The mounting conditions are shown below.





Up to two reflows are allowed.

Fig.41

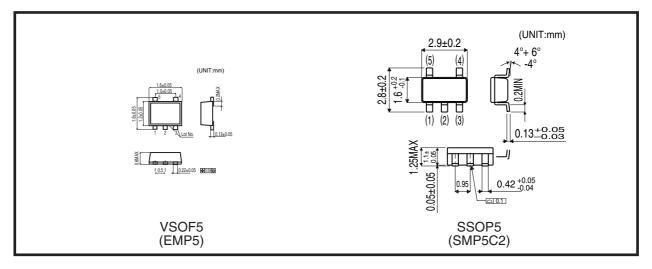
2)Flow soldering

| Treatment | Cond | dition |
|--------------------|-------------|------------|
| process | Temperature | Time |
| Preheating section | 150±10°C | 60 to 120s |
| Solder bath | Max. 260°C | Max. 10s |

3)Product storage conditions

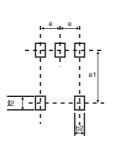
Store the products in an environment of 5 to 30°C in temperature and 70% RH or lower in humidity.

Dimension

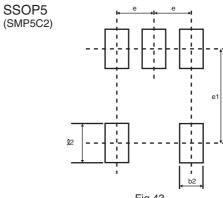


Reference land pattern

VSOF5 (EMP5)



Eig 40

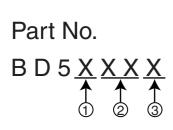


| | Fig | .42 | | | | Γιζ | J.43 | |
|------------|------------|-------------|------------|--|------------|------------|-------------|------------|
| | | | Unit:mm | | | | Unit:mm | |
| Lead pitch | Lead pitch | Land length | Land width | | Lead pitch | Lead pitch | Land length | Land width |
| e | e1 | _12 | b2 | | e | e1 | _12 | b2 |
| 0.50 | 1.35 | 0.35 | 0.25 | | 0.95 | 2.40 | 1.00 | 0.60 |

For actual designing, take the board density, mountability, dimension tolerance, etc. for optimization.

Part number and marking of samples

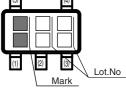
The BD52XX and BD53XX series products allow optimum selection of detection voltage, output circuit type and package according to the application.



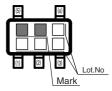
| Part No. | Specification | Contents |
|----------|---------------------|-----------------------------------------------------------------------------------|
| 1 | Output circuit type | 2 : Open drain output 3 : CMOS output |
| 2 | Detection voltage | Ex : VDET : described in each 0.1V step for 2.3V to 6.0V range (29 means 2.9V) |
| 3 | Package | G : SSOP5 (SMP5C2) FVE : VSOF5 (EMP5) |

| Marking | Voltage | Part No. |
|---------|---------|----------|---------|---------|----------|---------|---------|----------|---------|---------|----------|
| PW | 6.0V | BD5260 | PB | 4.1V | BD5241 | RW | 6.0V | BD5360 | RB | 4.1V | BD5341 |
| PV | 5.9V | BD5259 | PA | 4.0V | BD5240 | RV | 5.9V | BD5359 | RA | 4.0V | BD5340 |
| PU | 5.8V | BD5258 | MV | 3.9V | BD5239 | RU | 5.8V | BD5358 | QV | 3.9V | BD5339 |
| PT | 5.7V | BD5257 | MU | 3.8V | BD5238 | RT | 5.7V | BD5357 | QU | 3.8V | BD5338 |
| PS | 5.6V | BD5256 | MT | 3.7V | BD5237 | RS | 5.6V | BD5356 | QT | 3.7V | BD5337 |
| PR | 5.5V | BD5255 | MS | 3.6V | BD5236 | RR | 5.5V | BD5355 | QS | 3.6V | BD5336 |
| PQ | 5.4V | BD5254 | MR | 3.5V | BD5235 | RQ | 5.4V | BD5354 | QR | 3.5V | BD5335 |
| PP | 5.3V | BD5253 | MQ | 3.4V | BD5234 | RP | 5.3V | BD5353 | QQ | 3.4V | BD5334 |
| PN | 5.2V | BD5252 | MP | 3.3V | BD5233 | RN | 5.2V | BD5352 | QP | 3.3V | BD5333 |
| PM | 5.1V | BD5251 | MN | 3.2V | BD5232 | RM | 5.1V | BD5351 | QN | 3.2V | BD5332 |
| PL | 5.0V | BD5250 | MM | 3.1V | BD5231 | RL | 5.0V | BD5350 | QM | 3.1V | BD5331 |
| PK | 4.9V | BD5249 | ML | 3.0V | BD5230 | RK | 4.9V | BD5349 | QL | 3.0V | BD5330 |
| PJ | 4.8V | BD5248 | MK | 2.9V | BD5229 | RJ | 4.8V | BD5348 | QK | 2.9V | BD5329 |
| PH | 4.7V | BD5247 | MJ | 2.8V | BD5228 | RH | 4.7V | BD5347 | QJ | 2.8V | BD5328 |
| PG | 4.6V | BD5246 | MH | 2.7V | BD5227 | RG | 4.6V | BD5346 | QH | 2.7V | BD5327 |
| PF | 4.5V | BD5245 | MG | 2.6V | BD5226 | RF | 4.5V | BD5345 | QG | 2.6V | BD5326 |
| PE | 4.4V | BD5244 | MF | 2.5V | BD5225 | RE | 4.4V | BD5344 | QF | 2.5V | BD5325 |
| PD | 4.3V | BD5243 | ME | 2.4V | BD5224 | RD | 4.3V | BD5343 | QE | 2.4V | BD5324 |
| PC | 4.2V | BD5242 | MD | 2.3V | BD5223 | RC | 4.2V | BD5342 | QD | 2.3V | BD5323 |





BD52XXFVE/BD53XXFVE VSOF5 (EMP5)





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